

1. SCOPE

This specification provide the ratings and the requirements for high voltage silicon diode ESJA04-03A made by FUJI ELECTRIC CO.,LTD.

2. OUT VIEW

Shape and dimensions are described in Fig.3.

3. IDENTIFICATION

The diode shall be marked with Cathode Mark.

4. RATINGS AND CHARACTERISTICS

4.1 ABSOLUTE MAX. RATINGS. (Ta=25 °C unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Repetitive peak reverse voltage.		V_{RRM}	3	kVpeak
Non-Repetitive peak forward current.	50Hz Sine-half wave peak value	I_{FSM}	0.3	Apeak
Average forward current.	50Hz Sine Wave	I_{AV}	1	mA
Allowable junction temperature.		T_j	120	°C
Storage temperature range.		T_{stg}	-40~120	°C
Allowable operating case temperature.		T_c	100	°C

4.2 ELECTRICAL CHARACTERISTICS (Ta=25 °C unless otherwise noted.)

Items	Conditions	Symbols	Ratings	Units
Maximum forward voltage drop	$I_F=10mA$	V_F	12	V
Maximum reverse current	$V_R=3kV$	I_{R1}	2	μA
Maximum reverse current	$V_R=3kV, 100^\circ C$	I_{R2}	5	μA
Maximum reverse recovery time	$I_F=2mA, I_R=4mA$	t_{rr}	0.08	μS
Maximum junction capacitance	$f=1MHz, V_R=0V$	C_j	3	pF

4.3 MECHANICAL CHARACTERISTICS

Weight : Ca. 0.2 gr.

Vibration proof : 5 G

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Fuji Electric Co., Ltd.

DWG.NO.

H04-004-03

Typical

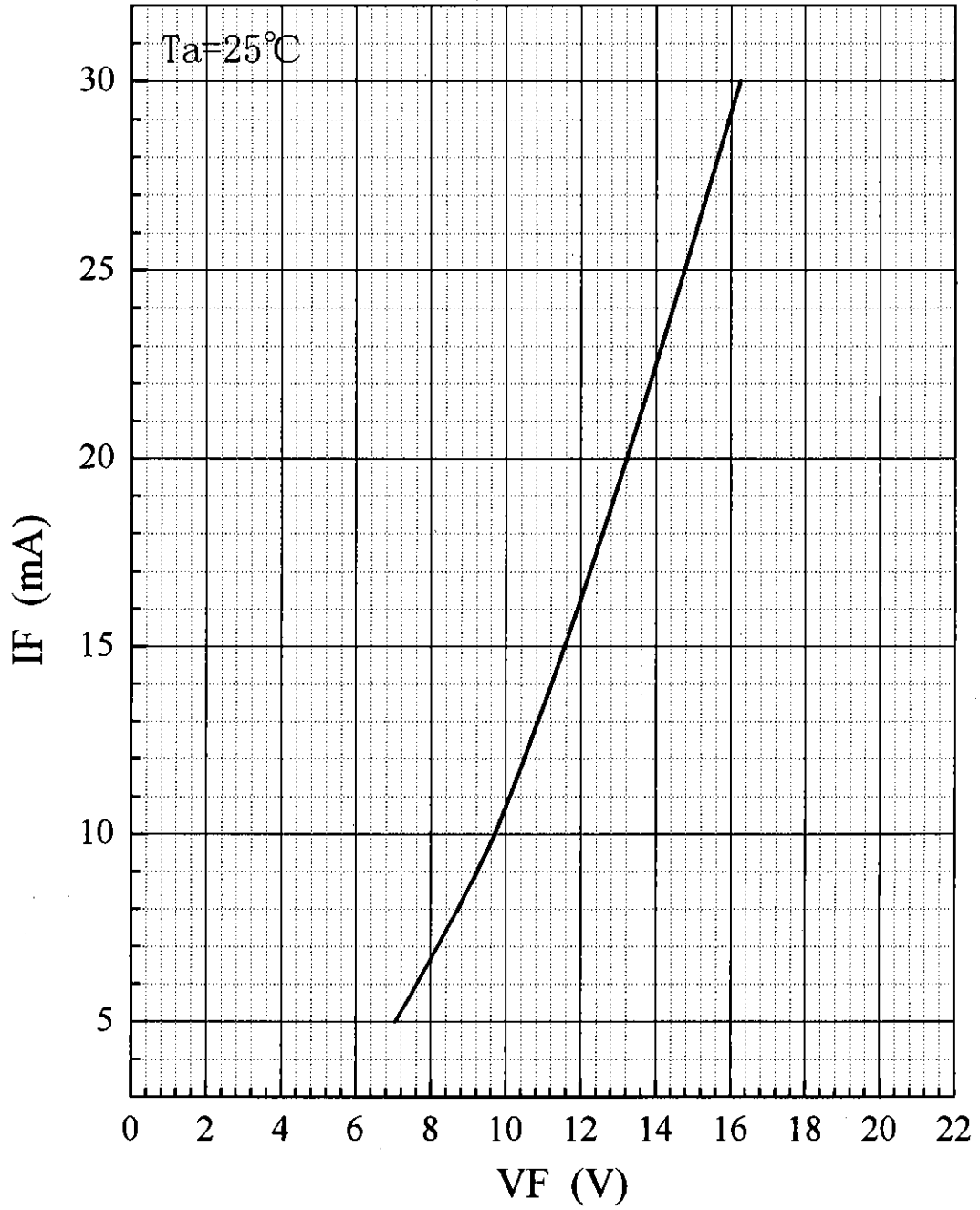


Fig.1 Forward characteristic[V_F - I_F]

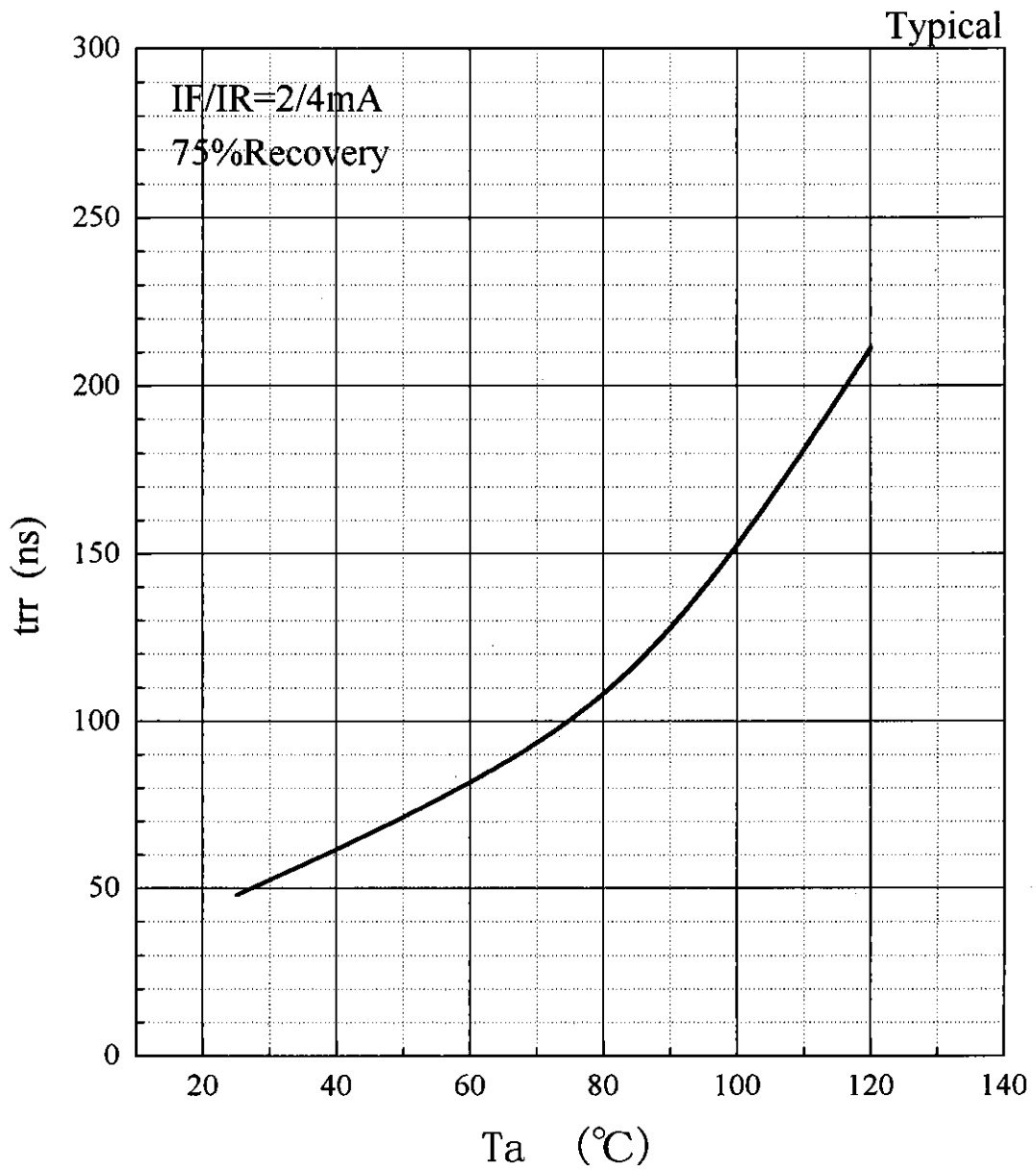


Fig.4 Reverse recovery time characteristic [Ta-trr]

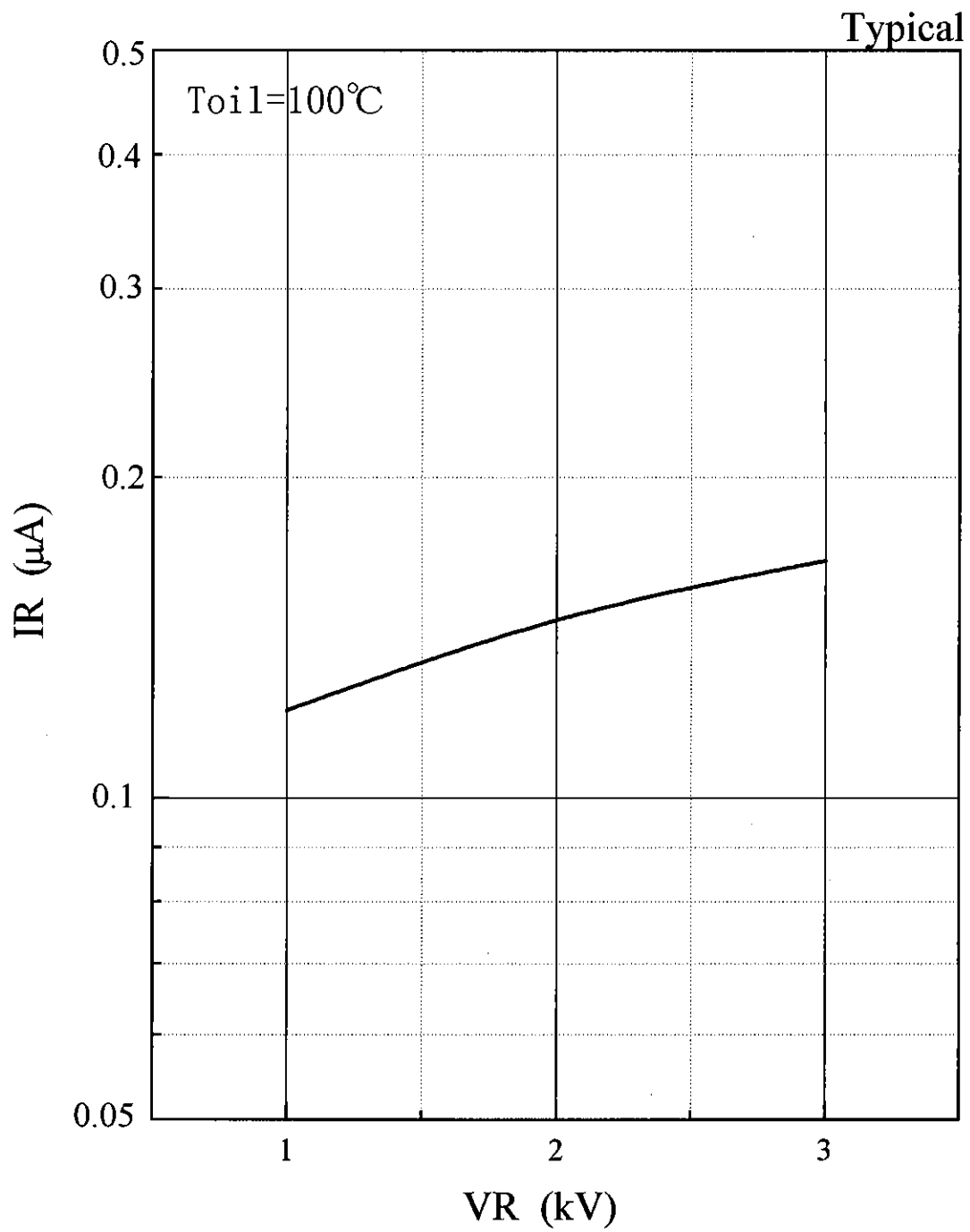


Fig.2 Reverse characteristic[VR-IR]

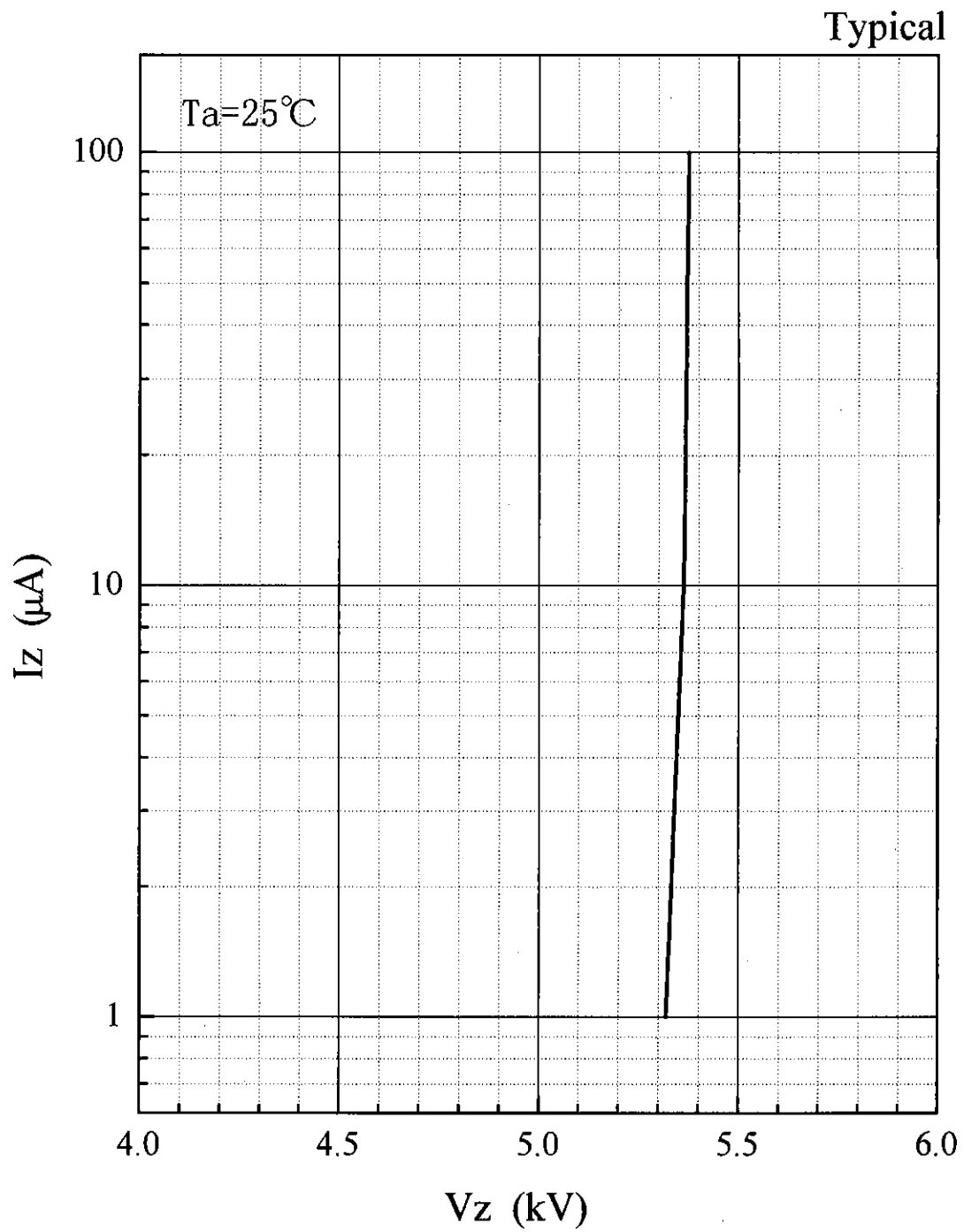
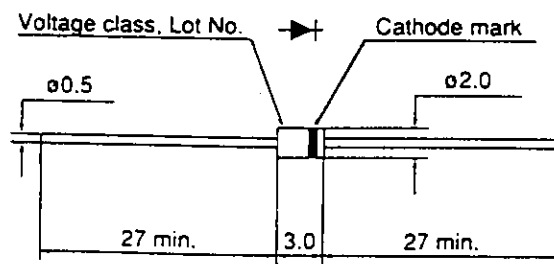


Fig.3 Avalanche characteristic [V_Z - I_Z]

Dimensions

Unit : mm

ESJA04-□□A



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